Silicon PNP Power Transistors 2SA1360

DESCRIPTION

・With TO-126 package
・Complement to type 2SC3423
・High transition frequency

APPLICATIONS

・Audio frequency amplifier applications

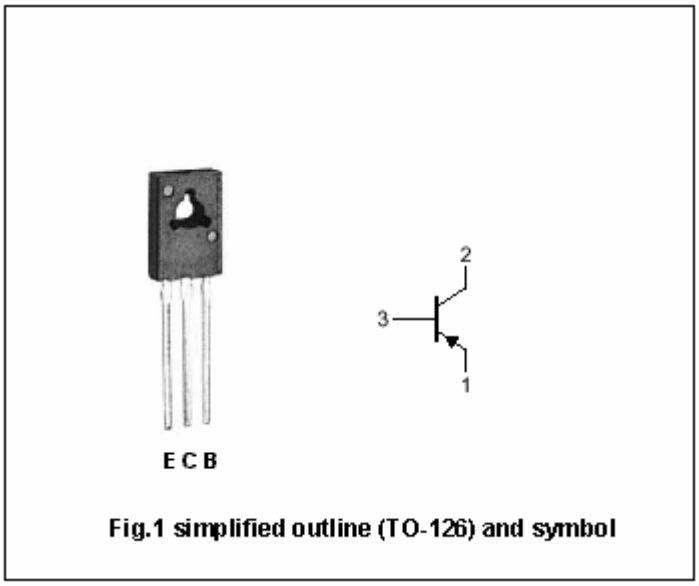

Fig.1 simplified outline (TO-126) and symbol

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-150	V
V_{CEO}	Collector-emitter voltage	Open base	-150	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-50	mA
I_B	Base current		-5	mA
P_D	Total power dissipation	T_a=25℃	1.2	W
		T_C=25℃	5	
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55～+150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-1mA ;I_B=0	-150			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-10mA; I_B=-1mA			-1.0	V
V_{BE}	Base-emitter on voltage	I_C=-10mA ; V_{CE}=-5V			-0.8	V
I_{CBO}	Collector cut-off current	V_{CB}=-150V; I_E=0			-0.1	μA
I_{EBO}	Emitter cut-off current	V_{EB}=-5V; I_C=0			-0.1	μA
h_{FE}	DC current gain	I_C=-10mA ; V_{CE}=-5V	80		240	
C_{ob}	Output capacitance	I_E=0 ; V_{CB}=-10V f=1MHz		2.5		pF
f_T	Transition frequency	I_C=-10mA ; V_{CE}=-10V		200		MHz

◆ **h_{FE} Classifications**

O	Y
80-160	120-240

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PACKAGE OUTLINE

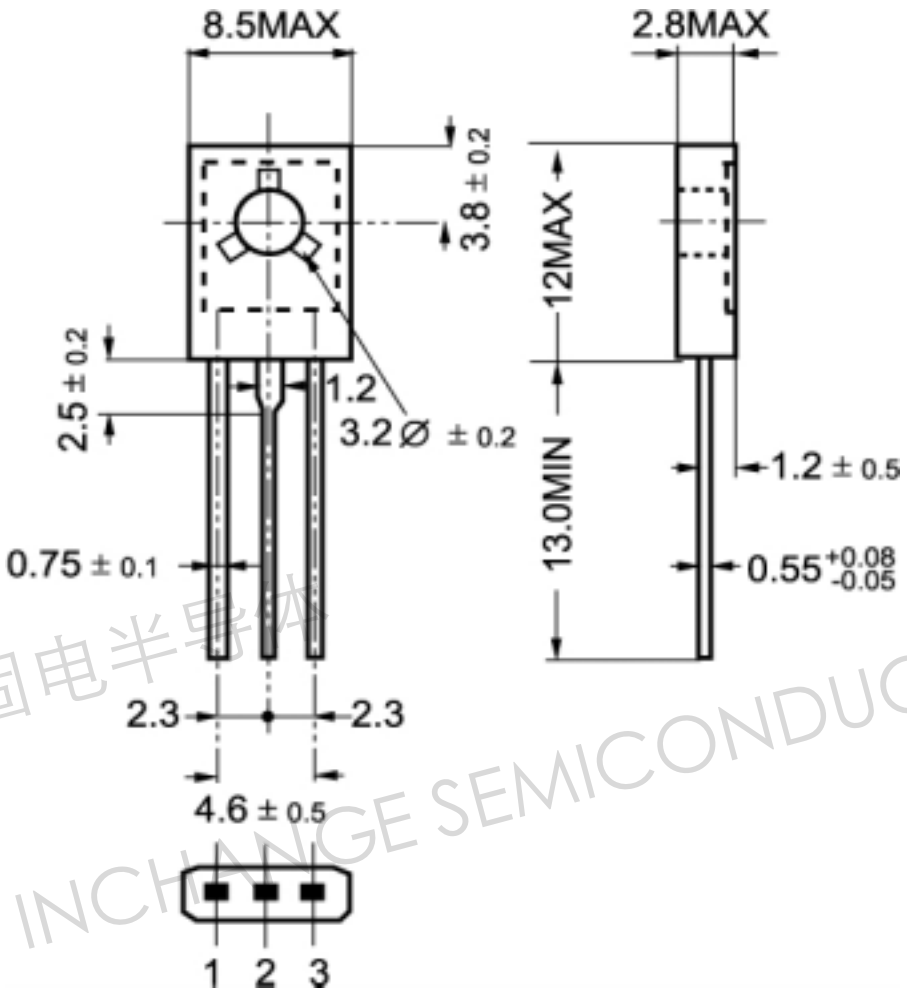

Fig.2 Outline dimensions

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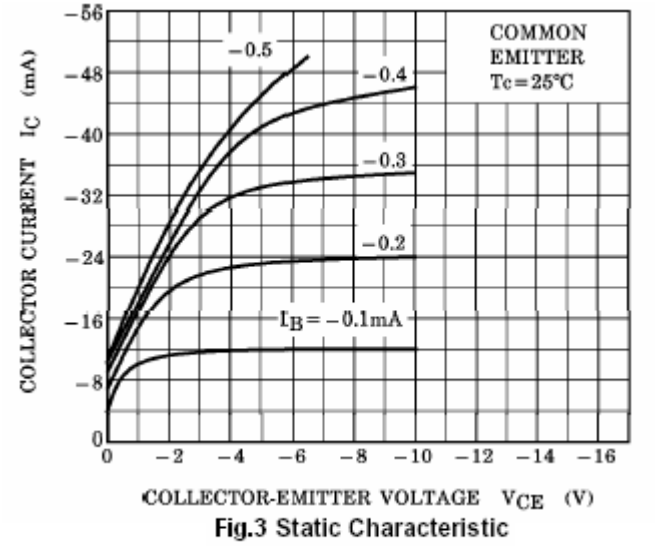

Fig.3 Static Characteristic

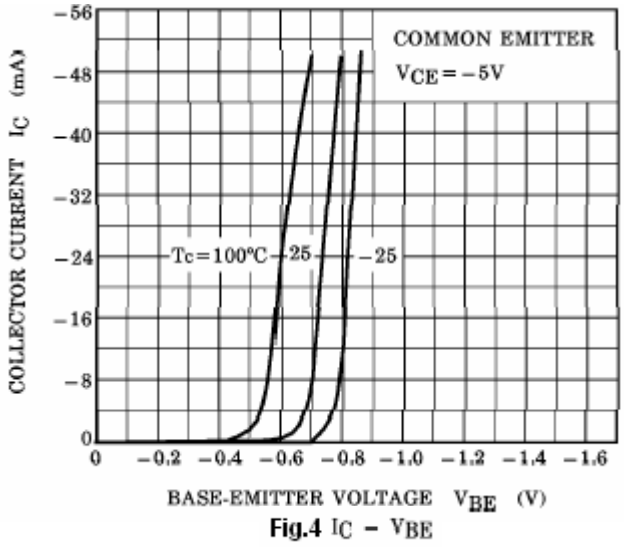

Fig.4 I_C - V_{BE}

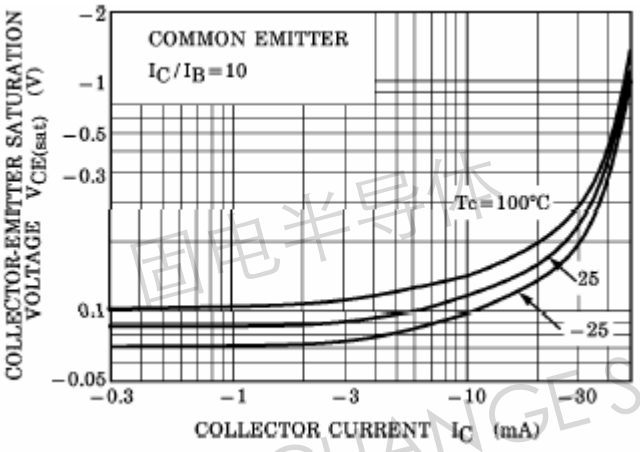

Fig.5 Collector-Emitter Saturation Voltage

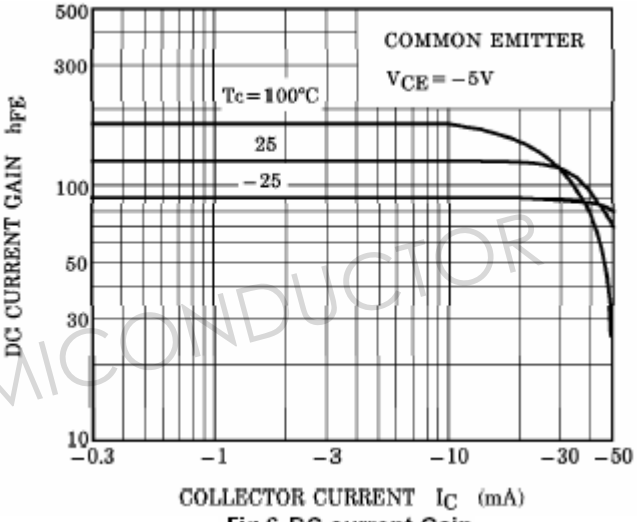

Fig.6 DC current Gain

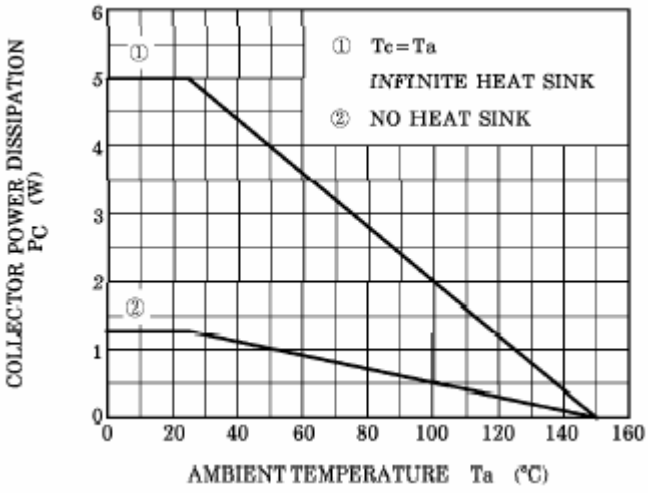

Fig.7 Power Derating